

Silicon TVS Diode

Features

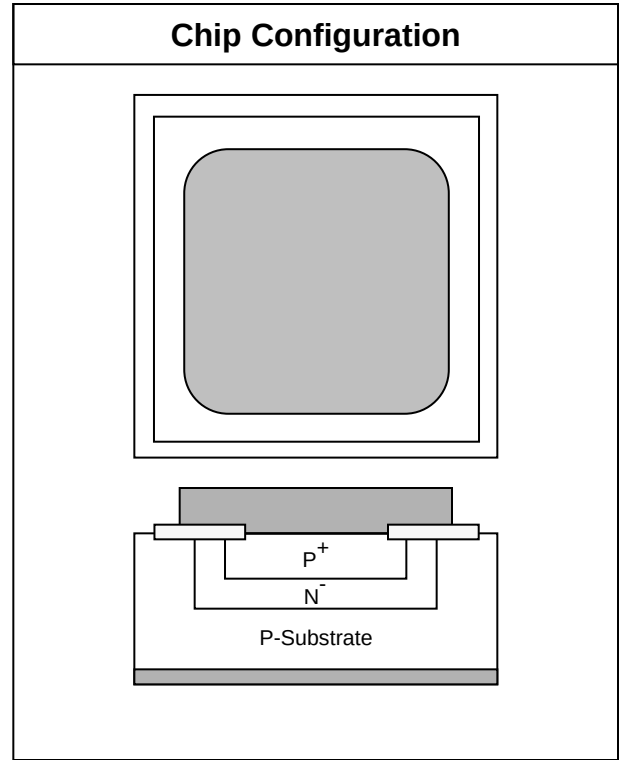
- ESD Protection
 - IEC 61000-4-2, Level 4
 - ±8kV (Contact Discharge), ±15kV (Air Discharge)
- Low leakage current

Structure

- Structure: Bidirectional
- Top electrode : Aluminum or Gold
- Bottom electrode : Gold

Size

- Chip size : 195(±20) μm x 195(±20) μm
- Thickness : 100(±20) μm
- Pad size : 140 μm x 140 μm



Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Maximum Rating	Unit
Power Dissipation	P_d	70	mW
ESD (IEC 61000-4-2, Contact)	V_{ESD}	± 8	kV
ESD (IEC 61000-4-2, Air)		±15	
Junction Temperature	T_j	150	°C

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 10\text{mA}$	14	-	21	V
Forward Leakage Current	I_F	$V_F = 7\text{V}$	-	-	100	nA
Reverse Voltage	V_Z	$I_R = 10\text{mA}$	14	-	19	V
Reverse Leakage Current	I_R	$V_Z = 7\text{V}$	-	-	100	nA